

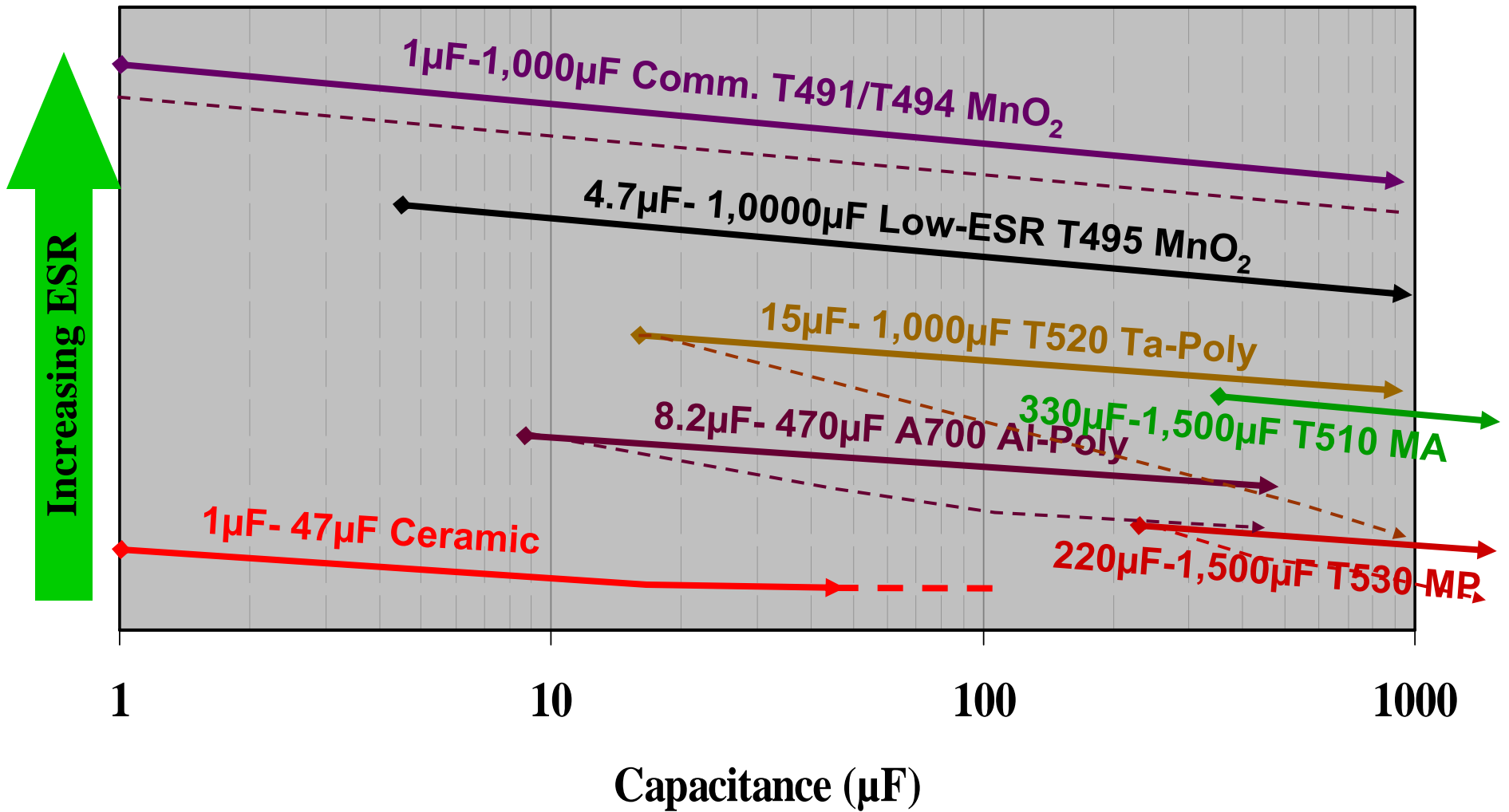


**Tantalum-Polymer
Capacitors for
Power Applications**

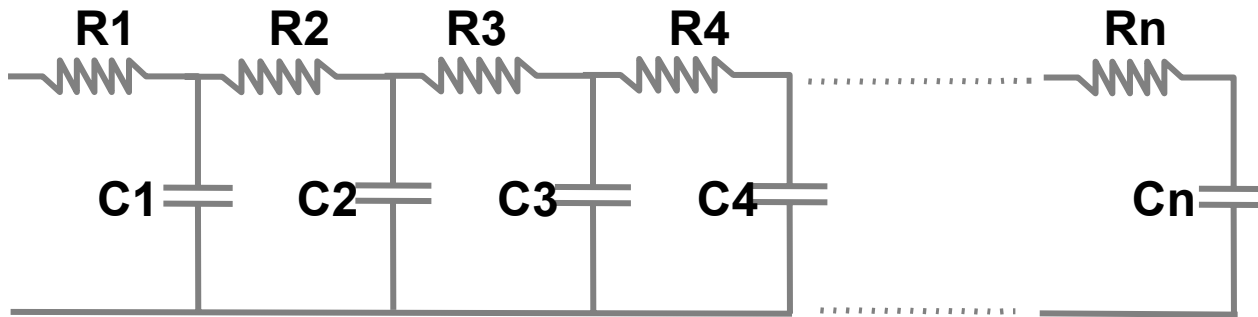
KEMET
CHARGED.™

TTI Web Broadcast

John D. Prymak
Applications Director



RC-Ladder Effects



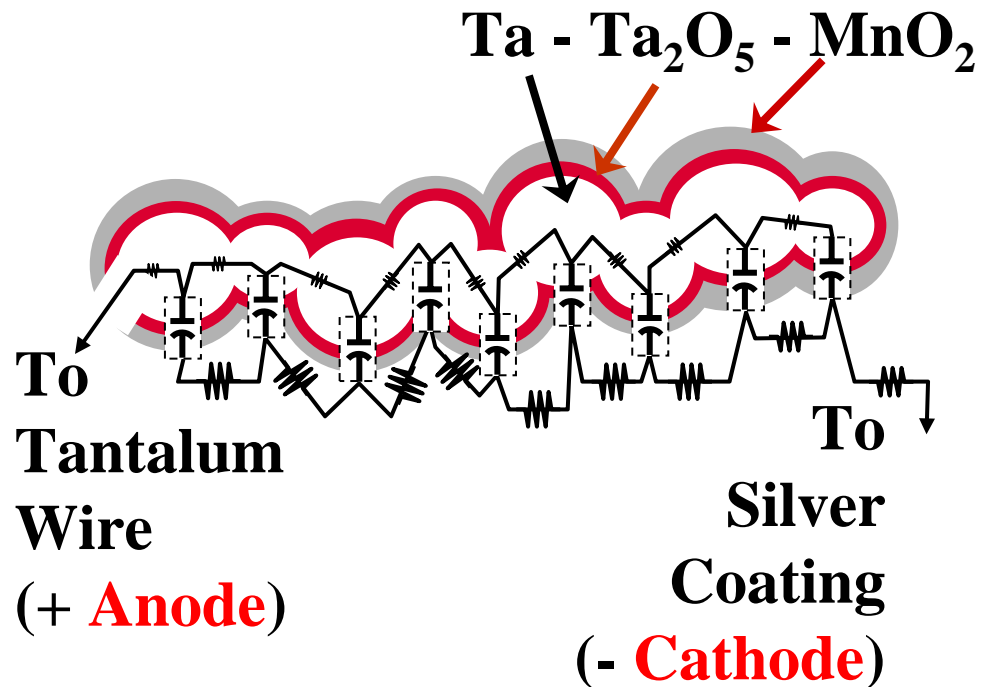
$tc1 = C1 \times R1$

$tc2 = C2 \times (R1 + R2)$

$tc3 = C3 \times (R1 + R2 + R3)$

$tcn = Cn \times (R1 + R2 + R3 \dots + Rn)$

RC-Ladder effects are factored by both capacitance and resistance.

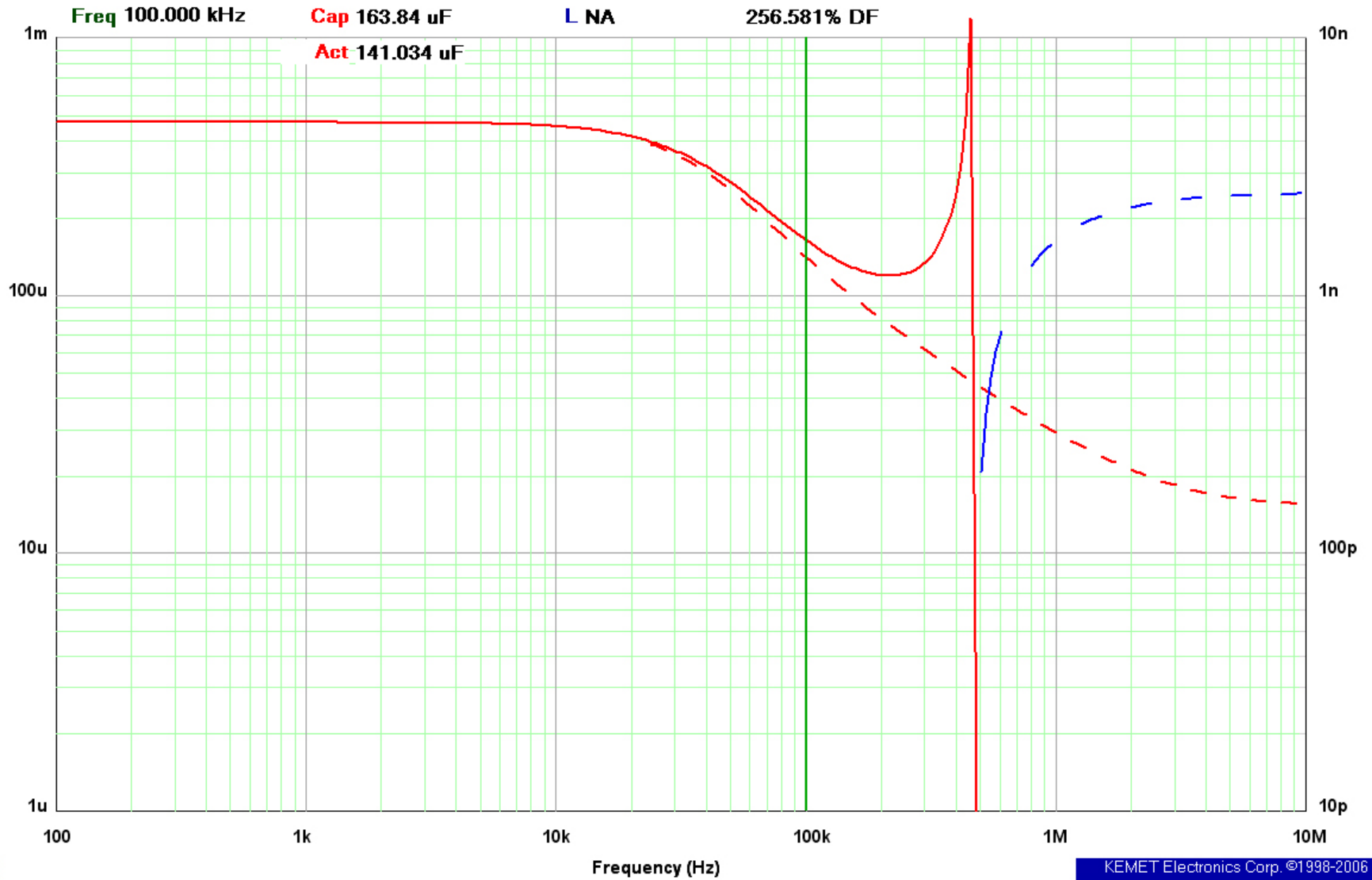


Electrolytic's Loss of Capacitance

MeasRed Capacitance

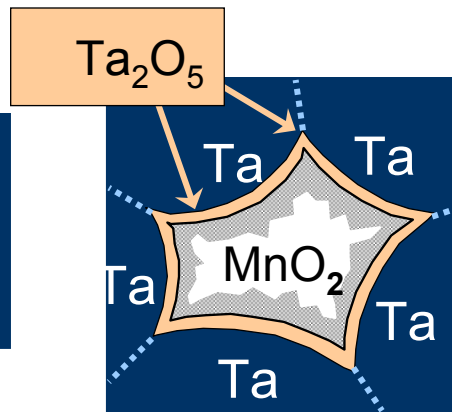
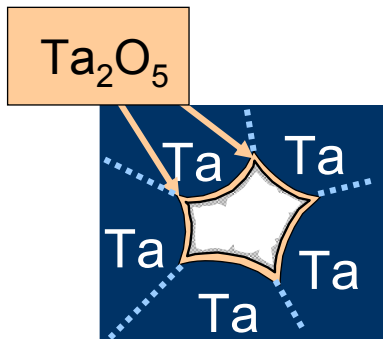
T495X477M006ATE030 @ +25°C with 3.15VDC Bias

MeasRed Inductance (H)



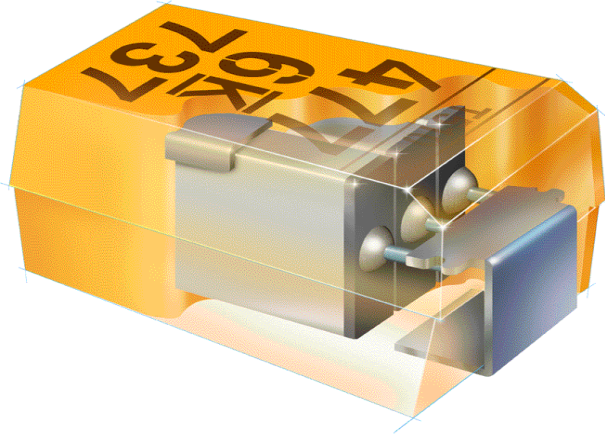
Quick review ESR Reduction in Tantalum ...

Lower Capacitance Loss with Frequency

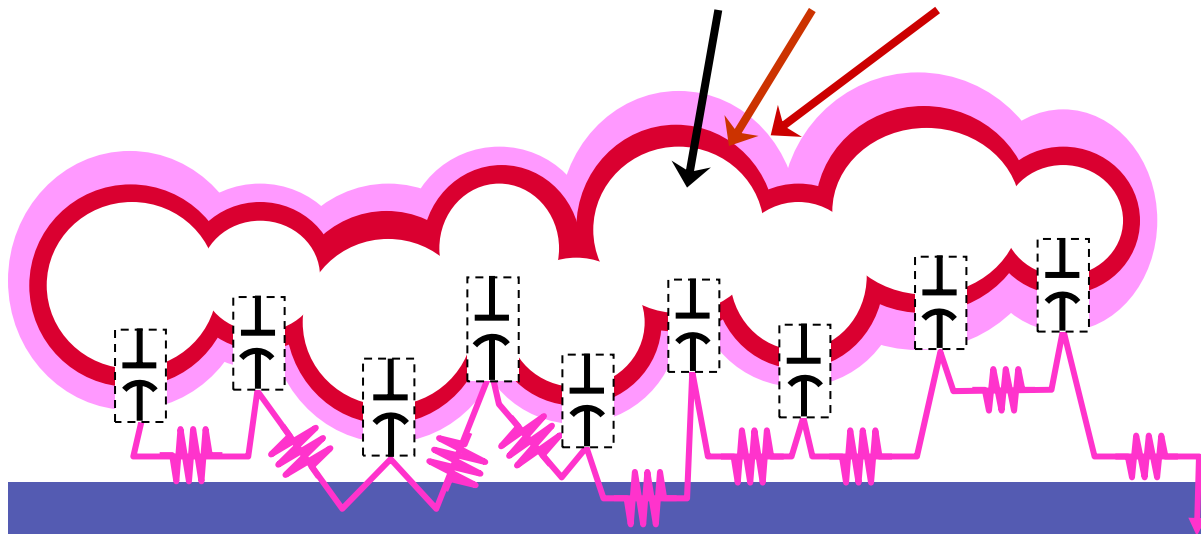


T495
Larger Pores
More MnO₂
Lower ESR

T510
Multiple-pellets
Lower ESR

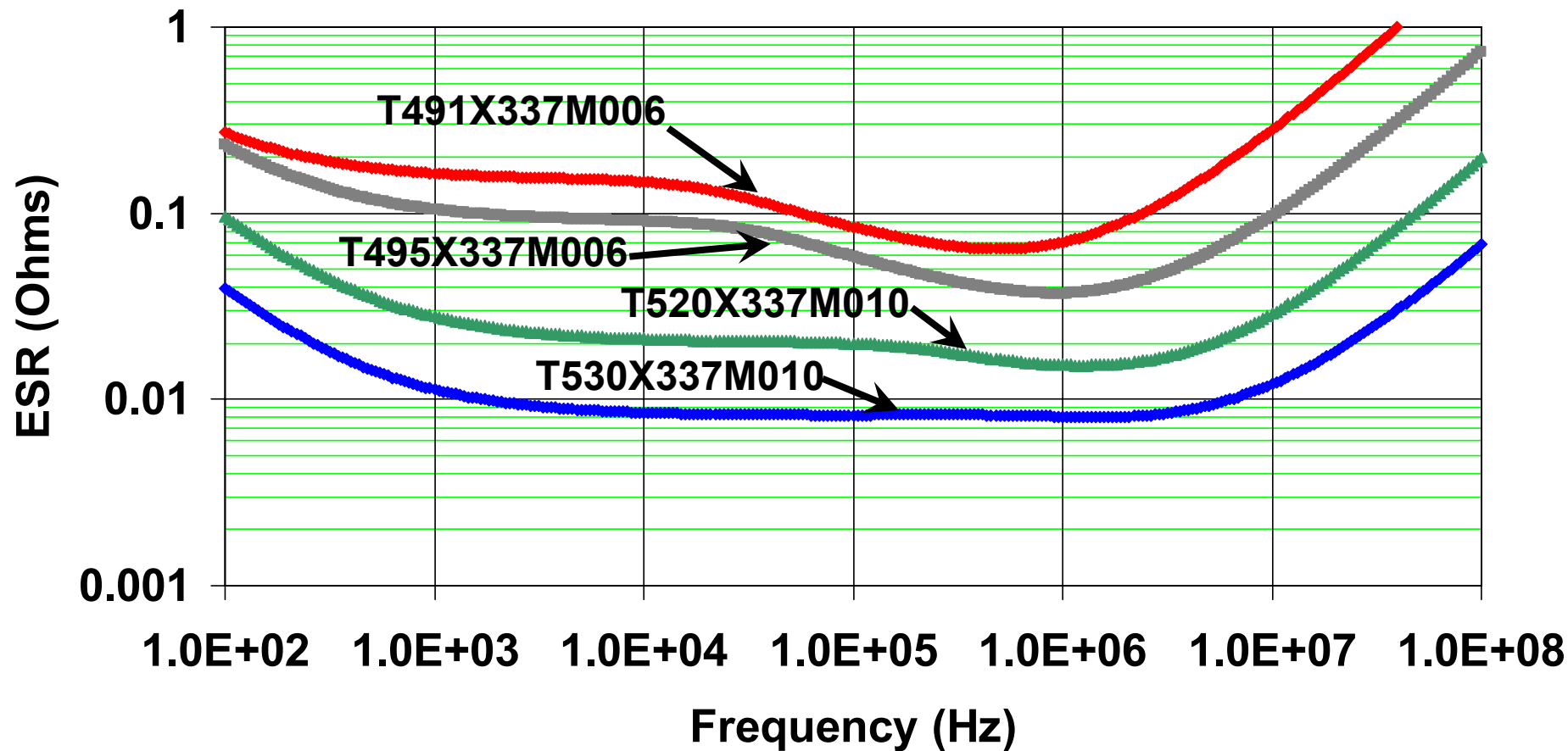


Ta - Ta₂O₅ - Polymer

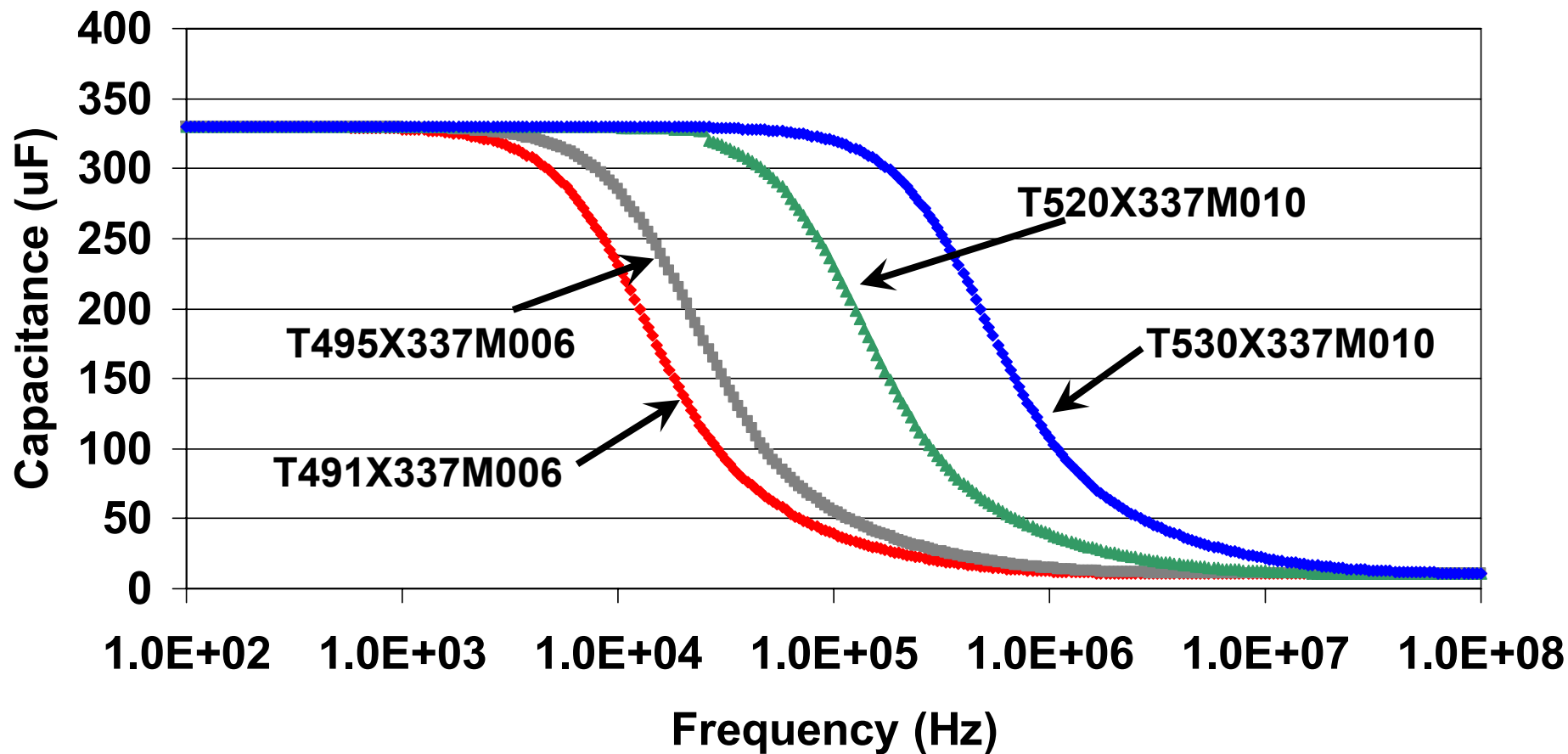


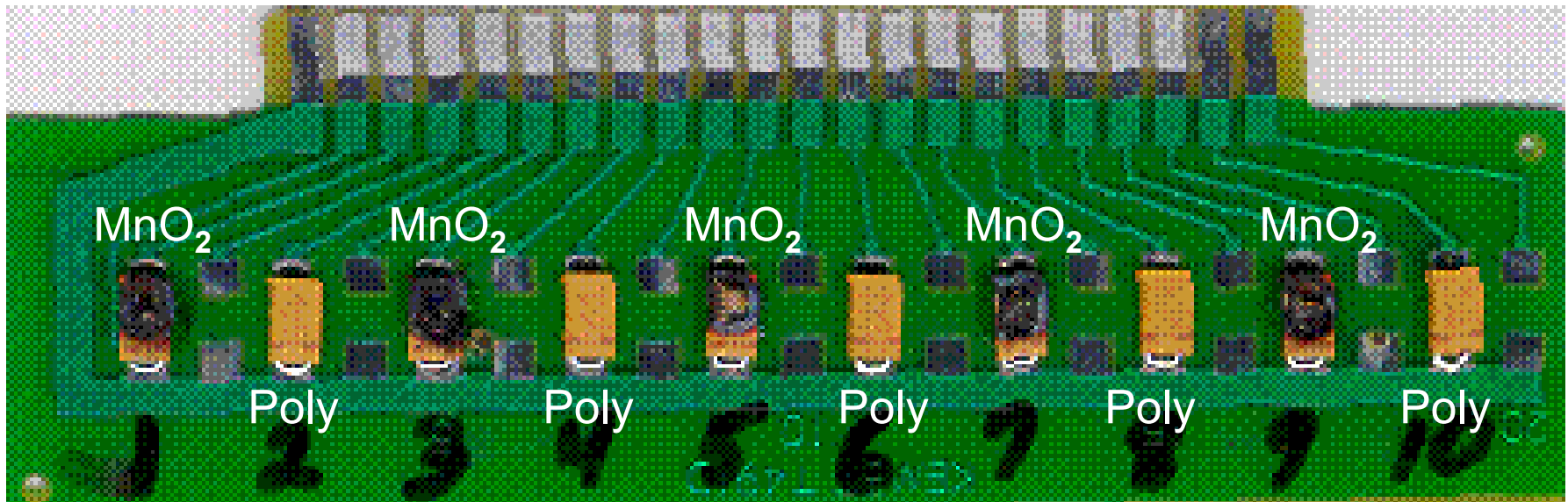
T520
Polymer
Replaces MnO₂
Lower ESR

330 μ F SMT Tantalum Chips



330 uF SMT Tantalum Chips

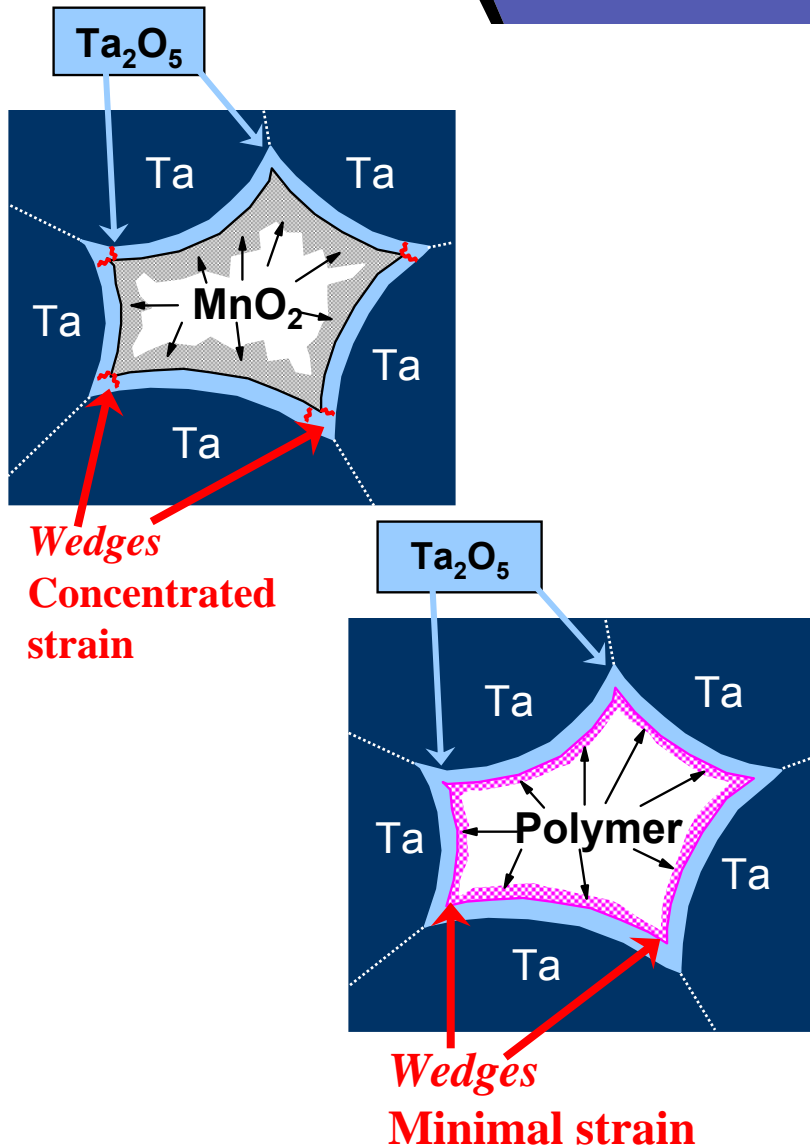




Test card with capacitors subjected to 2x Rated Voltage, applied with reverse polarity and > 20 amperes current capability.

Median Values

	Ta-MnO ₂	Ta-Poly KO V _R >10	Ta-Poly KO V _R ≤10
100 PPM FR % V _{Rated}	68%	126%	197%
@50% V _{Rated} FR(PPM)	9	0	0
@80% V _{Rated} FR(PPM)	458	4	1
@90% V _{Rated} FR(PPM)	1,700	12	2
@100% V _{Rated} FR(PPM)	6,310	35	8

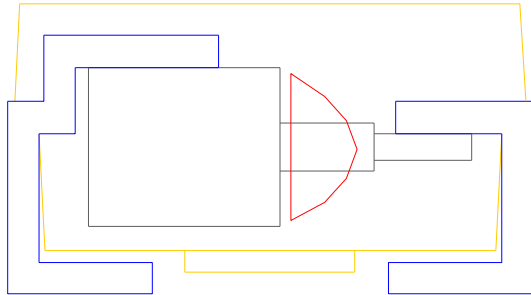


The MnO₂ filling this enclosure is a hard, crystalline material. Impregnation process involves dip at +25°C and conversion at +270°C. Forces in the “wedges” may be concentrated to cause defects.

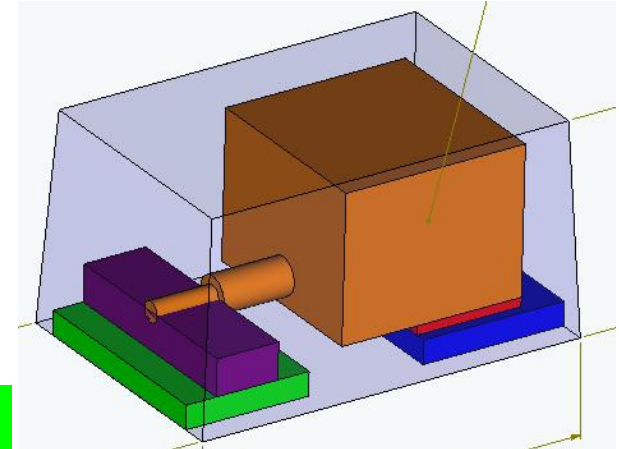
The polymer material is soft and **elastic**. The process is at or near room temperature. The forces generated because of mismatches in CTEs are insignificant when compared to MnO₂.

- There are several styles and values where the maximum ESRs are now at 4 milliohms with nominal values at 3 milliohms.
- As the ESR is being diminished, ESL is now of major concern.

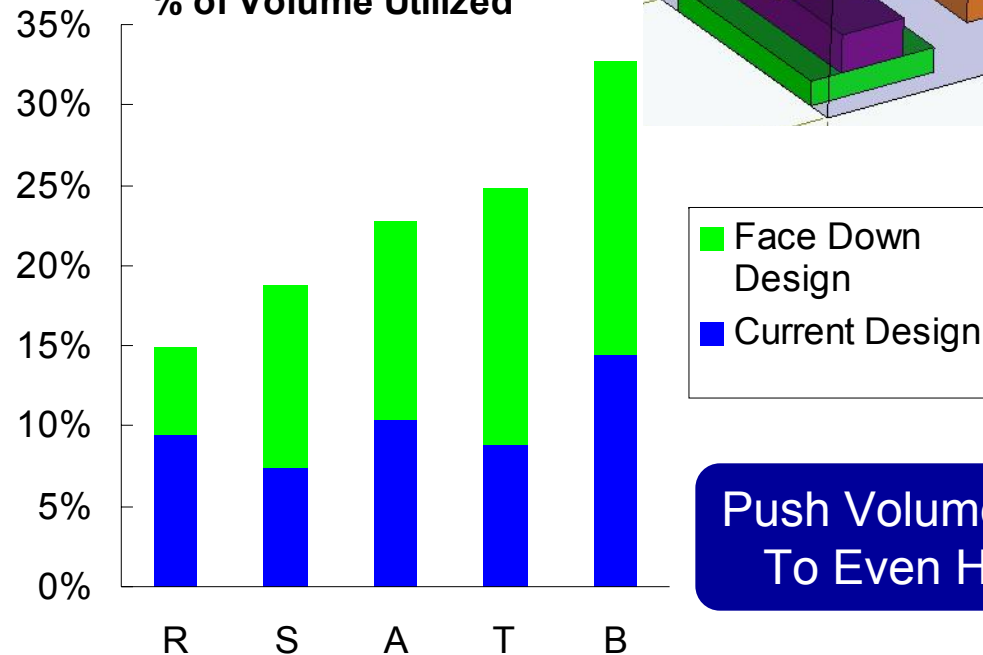
Standard Construction



Facedown Termination



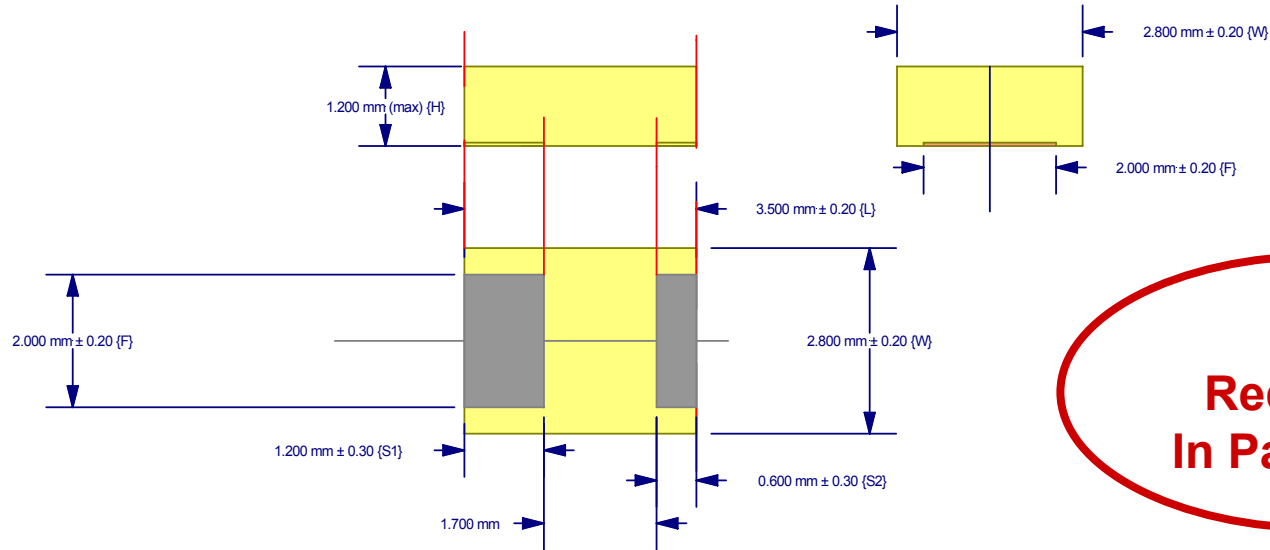
% of Volume Utilized



Push Volumetric Efficiency
To Even Higher Levels

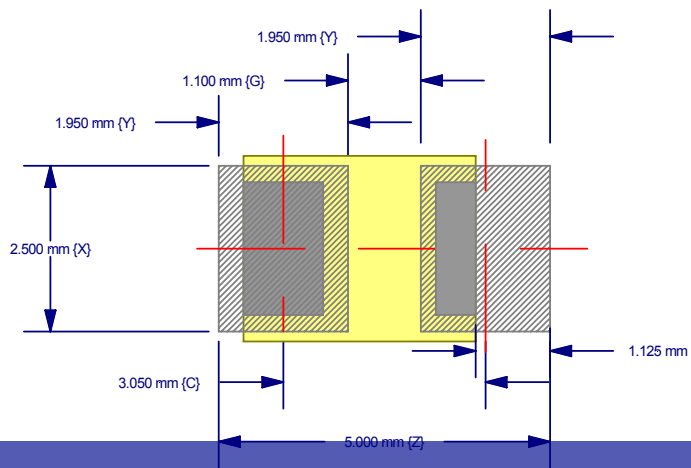
Recommended Pad Layouts – T Case

T3528-12 Face-Down

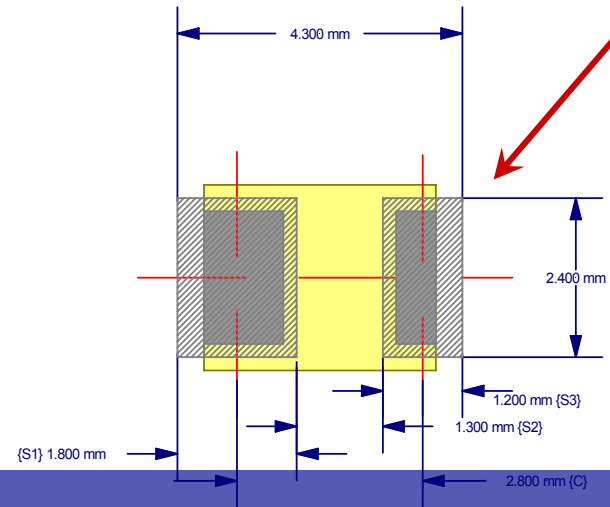


**20%
Reduction
In Pad Space**

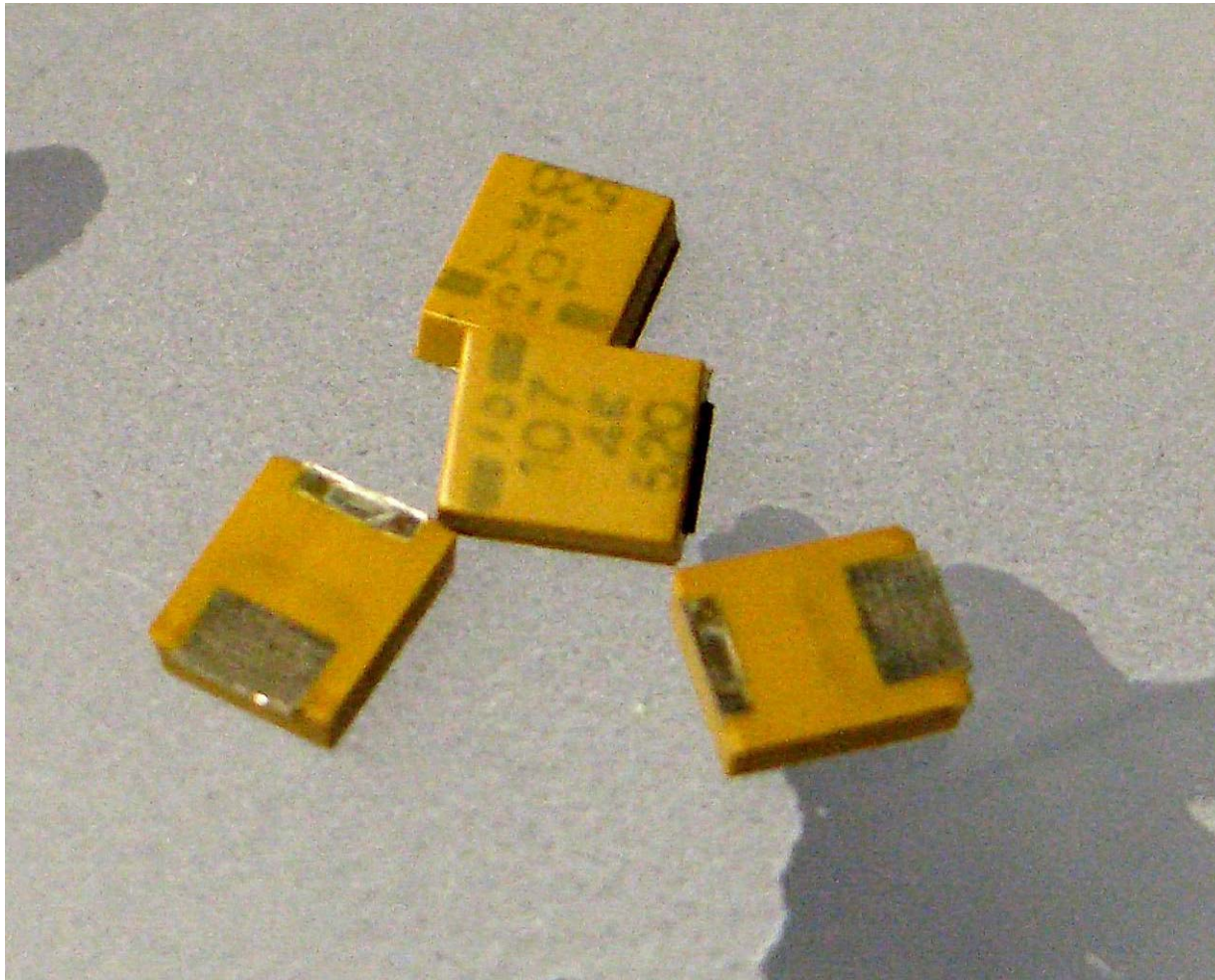
Using Standard 3528 Solder Pads



Using 3528/FD Solder Pads

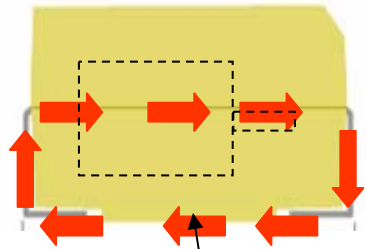


“T” Case (3528-12) / Facedown

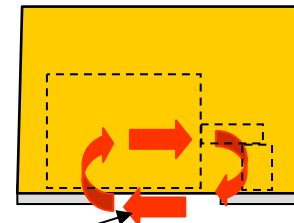


Reduced Current Loop Areas = Reduced ESL

STD
Ta/Poly Chip



Face-Down
Ta/Poly Chip



Reduction in current “loop area” creates proportional reduction in ESL.

Inductance for Solenoid:

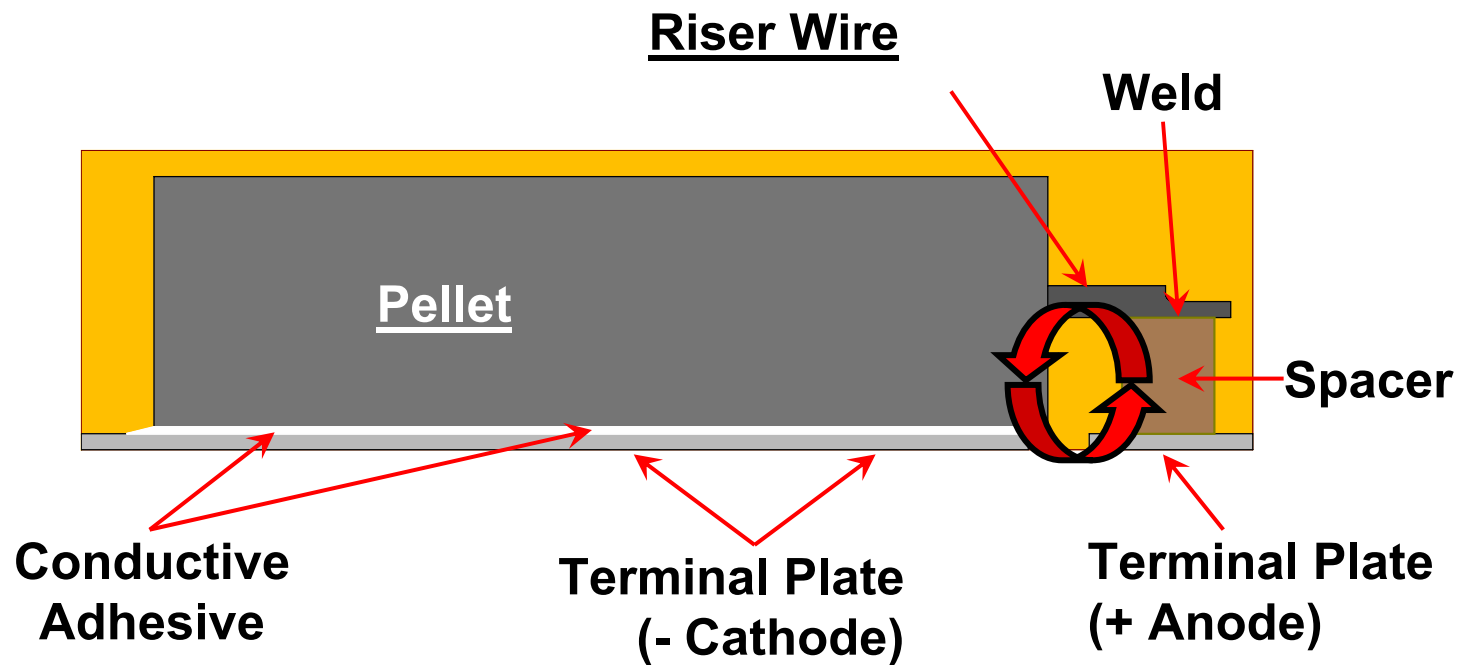
$$L = \mu_f n^2 Al$$

Where:

- L = inductance (henries)
- μ_f = permeability factor
- n = number turns per unit length
- A = Area of loop
- l = length

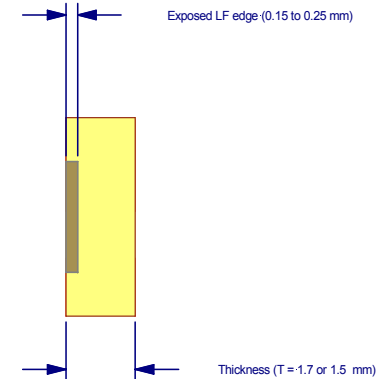
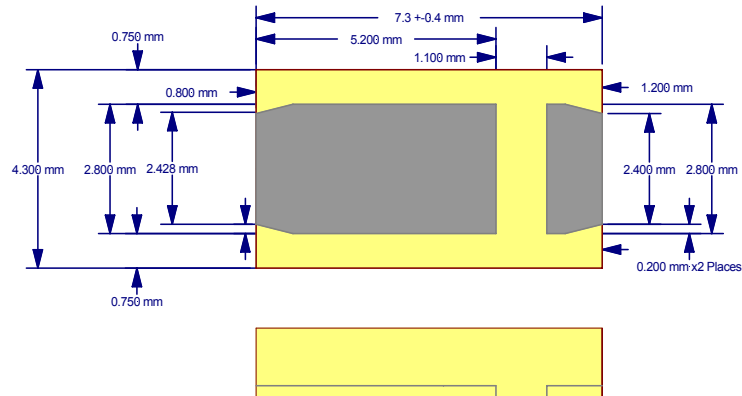
Inductance for loop:

$$L \propto A$$

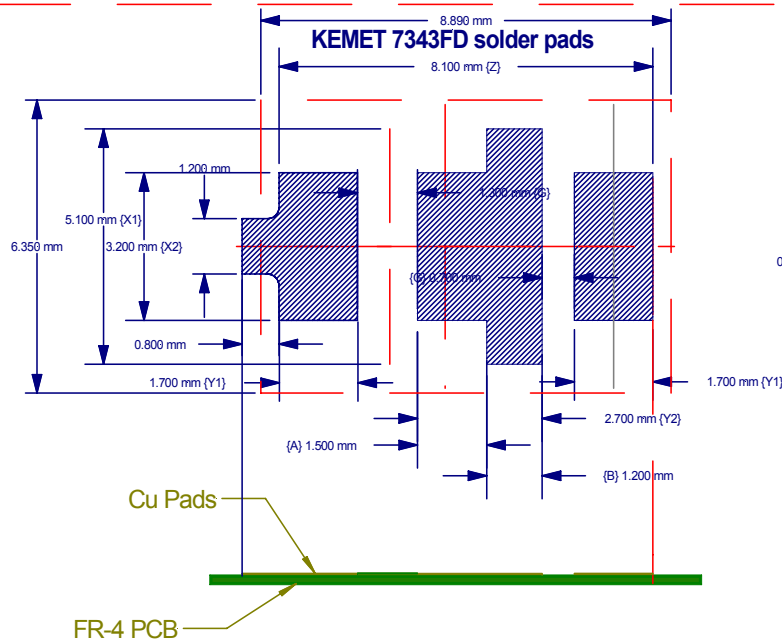


Recommended Pad Size – V,W,Z Case

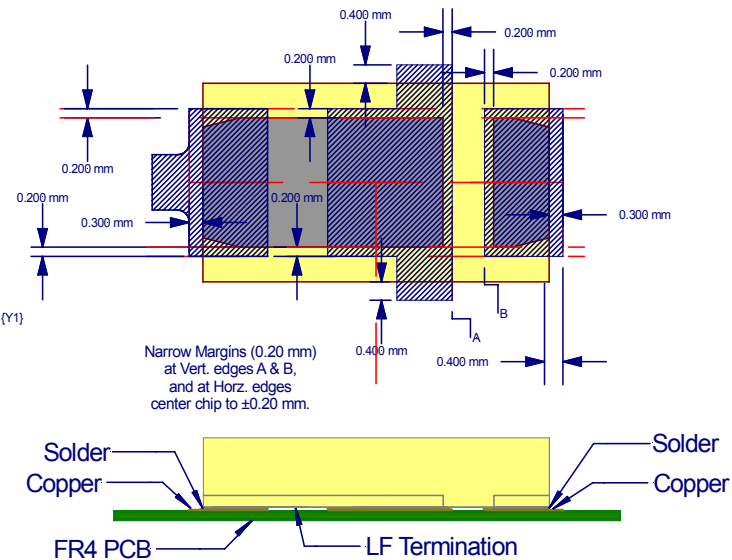
**T528/7343/FD (Pseudo 3-Terminal)
Facedown**



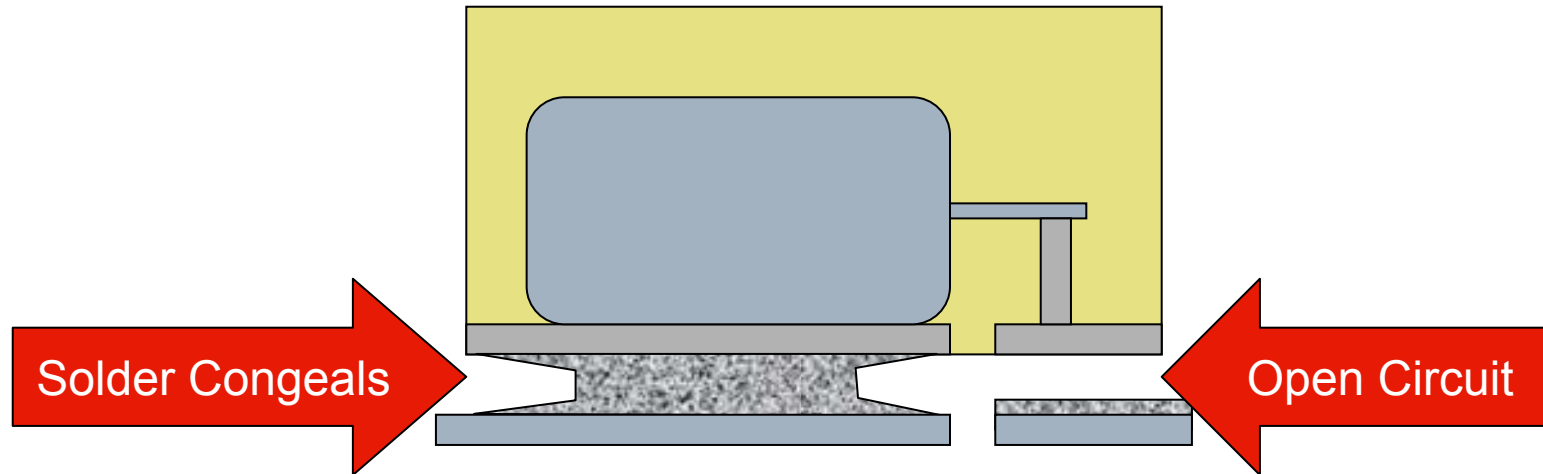
16 Mar 05

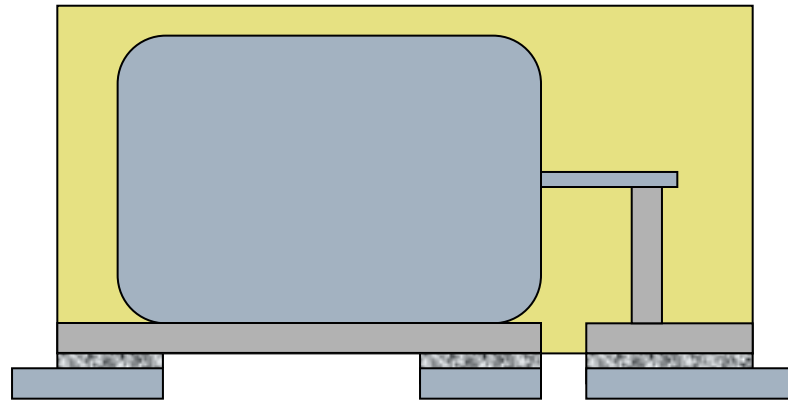


T528 using Sanyo TPL solder pads



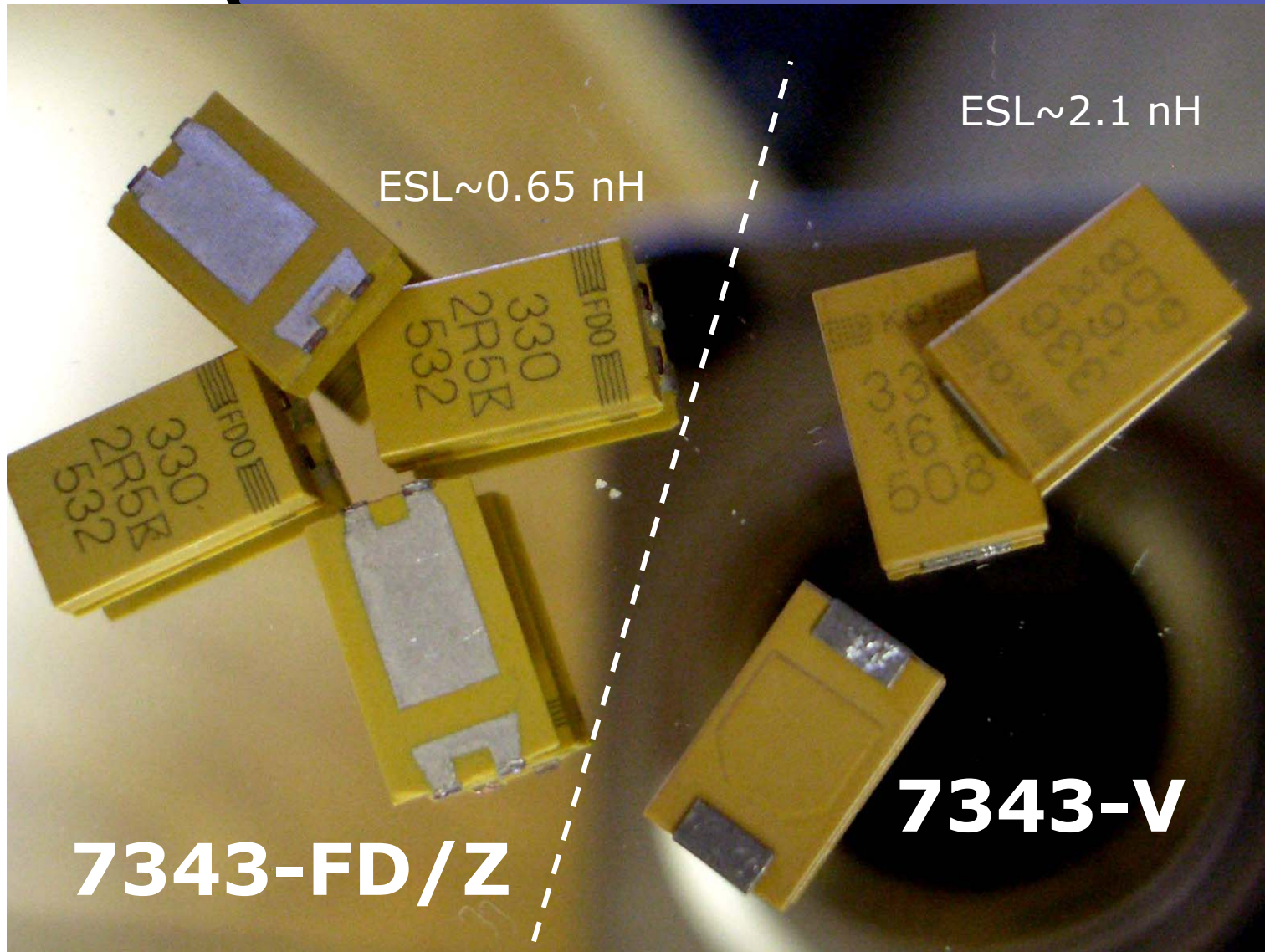
Solder Lift on Large Pad





Requires 3 Solder Pads to prevent large pad from lifting.

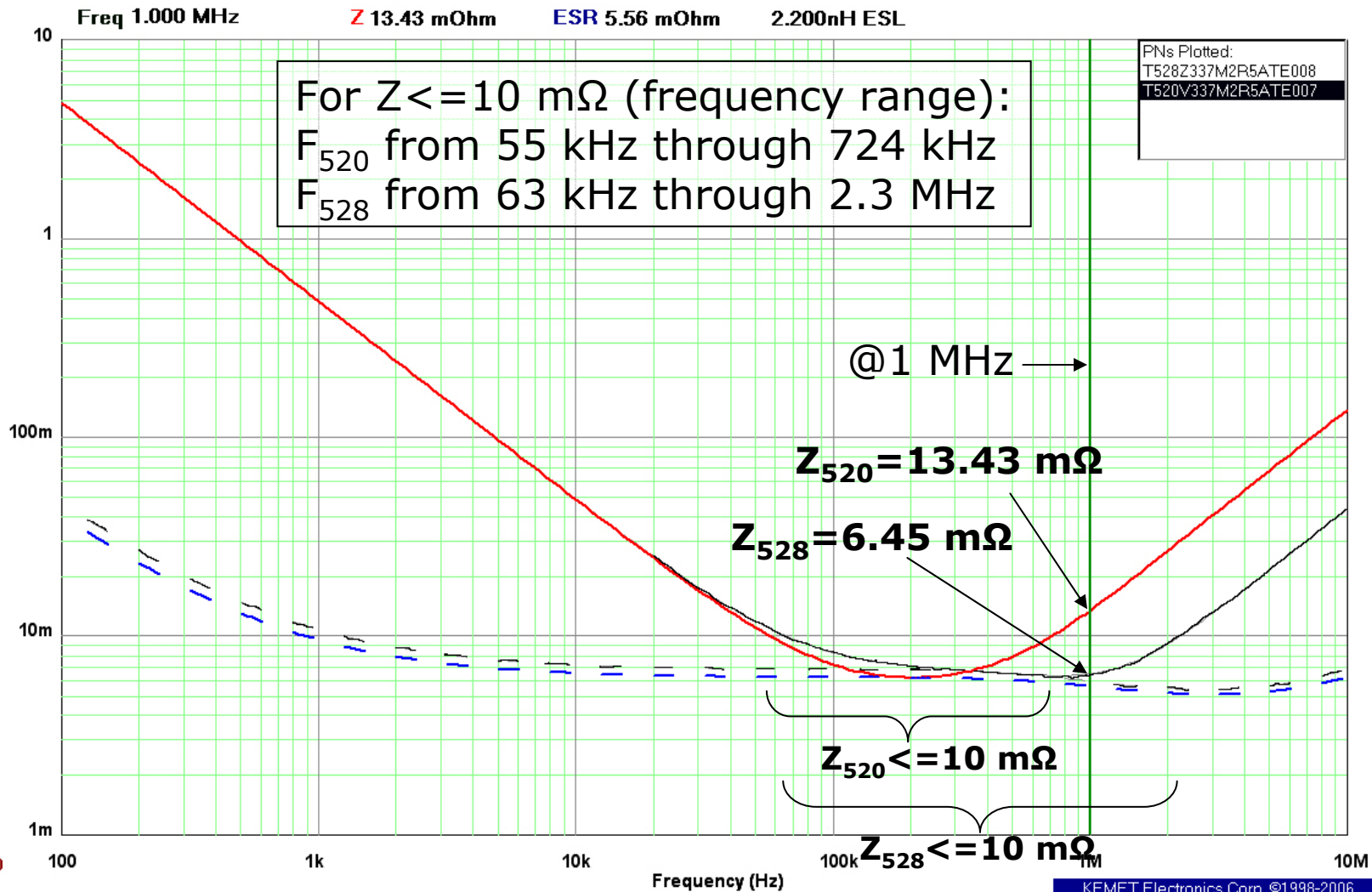
7343-FD/Z vs. 7343-V



T528 vs. T520 (Z/ESR) 330 uF / 2.5 WVDC

Impedance and ESR

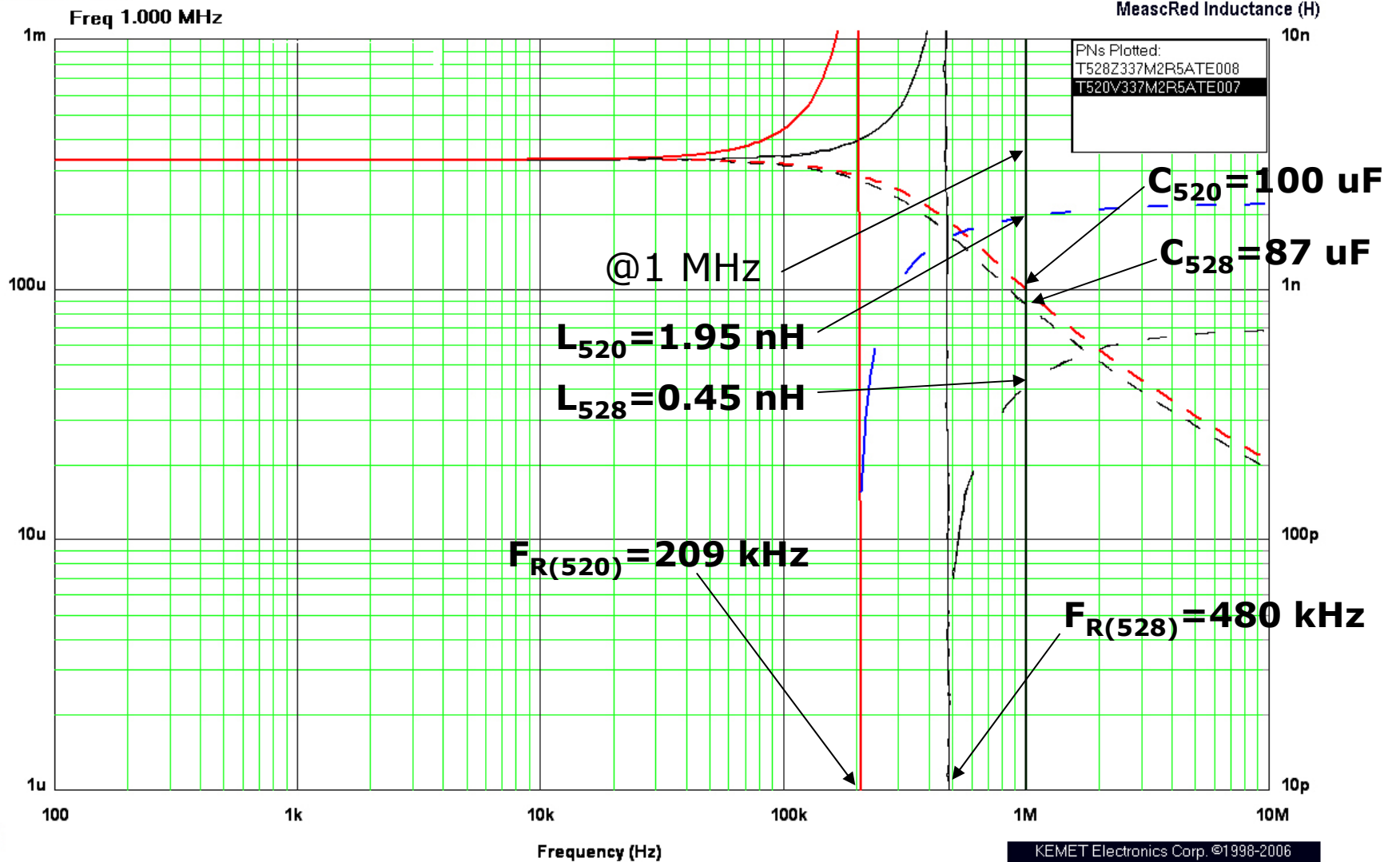
@ +25°C with 1.25VDC Bias



T528 vs. T520 (C/L) 330 μ F / 2.5 WVDC

@ +25°C with 1.25VDC Bias

MeasRed Capacitance

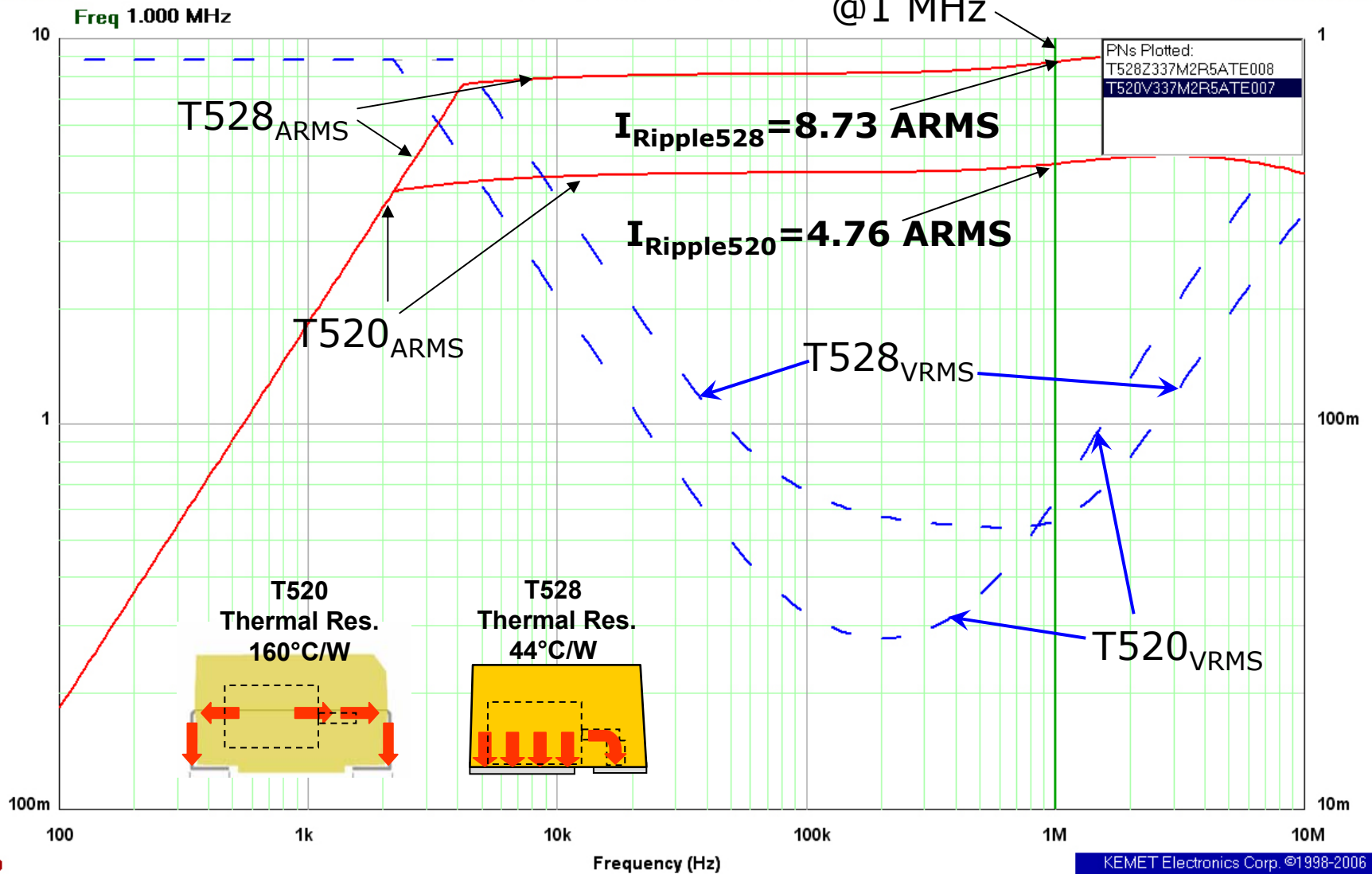


T528 vs. T520 (I/V) 330 uF / 2.5 WVDC

Max Current (ARMS)

@ +25°C with 1.25VDC Bias

Max Voltage (VRMS)



- Higher performance & efficiency (compared to MnO₂)
 - Lower ESRs
 - Better capacitance retention
 - Lowers piece count
- In conjunction with facedown designs
 - Lower ESL
 - Higher thermal conductivity
 - Higher ripple current
- Eliminates exothermic reactions at failure (ignitions)
- Benefits of Ta₂O₅ dielectrics
 - No voltage coefficients
 - No piezoelectric effects
 - High Capacitance/Volume
- T52x and T53x are RoHS compliant, and 260 capable.